

#10/B  
501.36931X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): IWASAKI, et al.

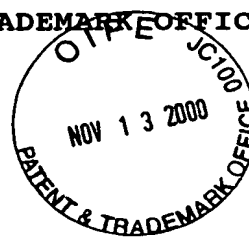
Serial No.: 09/255,856

Filed: February 23, 1999

For: SEMICONDUCTOR DEVICE WITH LAYERED INTERCONNECT  
STRUCTURE (AS AMENDED)

Group: 2813

Examiner: S. Smoot



11/28/00  
Shulh

AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

November 13, 2000

Sir:

In response to the Office Action mailed July 10, 2000,  
please amend the above-identified application as follows:

IN THE SPECIFICATION

Please delete the present title in its entirety, and  
substitute therefor the following:

--SEMICONDUCTOR DEVICE WITH LAYERED INTERCONNECT  
STRUCTURE--.

IN THE CLAIMS

✓  
Please cancel claim 7 without prejudice or disclaimer,  
and add the following new claims to the application:

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NOV 21 2000  
TC 2800 MAIL ROOM

--9. A semiconductor device having a layered  
interconnection structure including a copper film or a

11/15/2000 AZERGAW1 00000040 09255856

02 FC:102  
03 FC:103

80.00 OP  
144.00 OP